



VOIS (CHINA) LTD

RB751G-40 Schottky barrier Diodes

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

SOD-723



MARKING: 5

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ C$

Parameter	Symbol	Limits		Unit
Peak reverse voltage	V_{RM}	40		V
DC reverse voltage	V_R	30		V
Mean rectifying current	I_o	30		mA
Peak forward surge current	I_{FSM}	200		mA
Junction temperature	T_j	125		°C
Storage temperature	T_{stg}	-40~125		°C

Electrical Ratings @ $T_A=25^\circ C$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.37	V	$I_F=1\text{mA}$
Reverse current	I_R			0.5	μA	$V_R=30\text{V}$
Capacitance between terminals	C_T		2		pF	$V_R=1\text{V}, f=1\text{MHz}$

Typical Characteristics

RB751G-40

●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

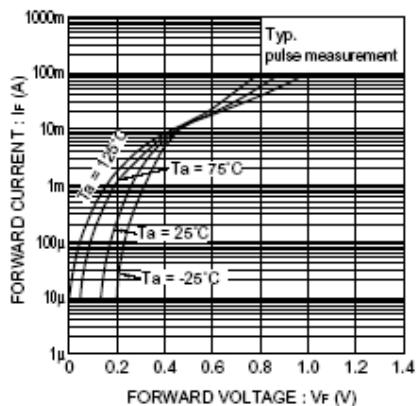


Fig. 1 Forward characteristics

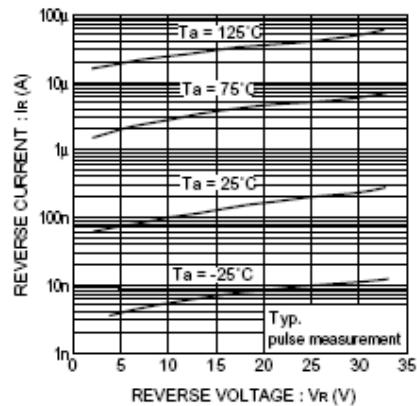


Fig. 2 Reverse characteristics

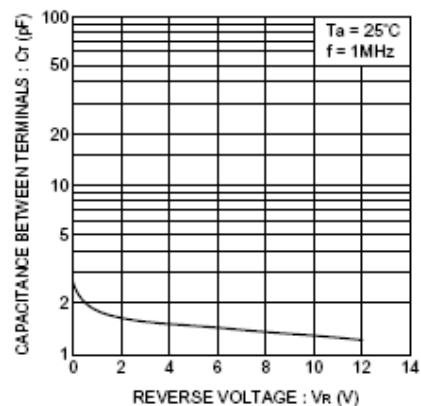


Fig. 3 Capacitance between terminals characteristics